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TITLE: DRY ETCHING METHOD

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ABSTRACT:

PURPOSE: To prevent or remove the etching residue or produced polysilicon and
to suppress the etching of a semiconductor material by etching the
semiconductor material with gas which contains at least C, F, O and compounds
simultaneously contained as indispensable components.

CONSTITUTION: Perfluoroepoxides such as
CF<SB>2</SB>CF<SB>2</SB>O or perfluoro
cyclic ethers such as CF<SB>2</SB>CF<SB>2</SB>CH<SB>2</SB> is suitable gas, and
a mixture of two or more gases containing mainly solely any of them or

hexafluoropropylene oxide is employed. When trifluoromethane is mixed at the
etching time of SiO<SB>2</SB>, PSG for these compounds, the formation of
polymer can be particularly suppressed while holding the selectivity of the
primary Si and a photoresist, and when Cl<SB>2</SB> is mixed at the etching
time of the polysilicon or metallic film, the etching of high selectivity can
be performed at a high speed, and when suitable amount is mixed with
hexafluoropropylene oxide, it is similarly effective.